Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	CANbus, EBI/EMI, I²C, IrDA, LINbus, MMC/SD, QSPI, SAI, SPI, SWPMI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, LCD, PWM, WDT
Number of I/O	83
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	320K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-UFBGA, WLCSP
Supplier Device Package	100-WLCSP (4.62x4.14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l496vgy6tr

without having any impact on the timing of “injected” conversions

– “injected” conversions for precise timing and with high conversion priority

3.25 Random number generator (RNG)

All devices embed an RNG that delivers 32-bit random numbers generated by an integrated analog circuit.

3.26 Digital camera interface (DCMI)

The devices embed a camera interface that can connect with camera modules and CMOS sensors through an 8-bit to 14-bit parallel interface, to receive video data. The camera interface can sustain a data transfer rate up to 54 Mbyte/s at 54 MHz. It features:

- Programmable polarity for the input pixel clock and synchronization signals
- Parallel data communication can be 8-, 10-, 12- or 14-bit
- Supports 8-bit progressive video monochrome or raw bayer format, YCbCr 4:2:2 progressive video, RGB 565 progressive video or compressed data (like JPEG)
- Supports continuous mode or snapshot (a single frame) mode
- Capability to automatically crop the image

3.27 Timers and watchdogs

The STM32L496xx includes two advanced control timers, up to nine general-purpose timers, two basic timers, two low-power timers, two watchdog timers and a SysTick timer. The table below compares the features of the advanced control, general purpose and basic timers.

Table 10. Timer feature comparison

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/ compare channels	Complementary outputs
Advanced control	TIM1, TIM8	16-bit	Up, down, Up/down	Any integer between 1 and 65536	Yes	4	3
General-purpose	TIM2, TIM5	32-bit	Up, down, Up/down	Any integer between 1 and 65536	Yes	4	No
General-purpose	TIM3, TIM4	16-bit	Up, down, Up/down	Any integer between 1 and 65536	Yes	4	No
General-purpose	TIM15	16-bit	Up	Any integer between 1 and 65536	Yes	2	1

Table 13. SAI implementation

SAI features(1)	SAI1	SAI2
I2S, LSB or MSB-justified, PCM/DSP, TDM, AC'97	X	X
Mute mode	X	X
Stereo/Mono audio frame capability.	X	X
16 slots	X	X
Data size configurable: 8-, 10-, 16-, 20-, 24-, 32-bit	X	X
FIFO Size	X (8 Word)	X (8 Word)
SPDIF	X	X

1. X: supported

3.34 Single wire protocol master interface (SWPMI)

The Single wire protocol master interface (SWPMI) is the master interface corresponding to the Contactless Frontend (CLF) defined in the ETSI TS 102 613 technical specification. The main features are:

- full-duplex communication mode
- automatic SWP bus state management (active, suspend, resume)
- configurable bitrate up to 2 Mbit/s
- automatic SOF, EOF and CRC handling

SWPMI can be served by the DMA controller.

3.35 Controller area network (CAN)

The two CANs are compliant with the 2.0A and B (active) specifications with a bit rate up to 1Mbit/s. They can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. Each CAN has three transmit mailboxes, two receive FIFOS with 3 stages and 28 shared scalable filter banks (all of them can be used even if one CAN is used). 256 bytes of SRAM are allocated for each CAN.

Table 15. STM32L496xx pin definitions (continued)

Pin Number									Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
LQFP64	WLCSP100	WLCSP100_SMPS	LQFP100	UFBGA132	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS					Alternate functions	Additional functions
45	C1	C1	71	A12	104	104	D13	D13	PA12	I/O	FT_u	-	TIM1_ETR, SPI1_MOSI, USART1_RTS_DE, CAN1_TX, OTG_FS_DP, EVENTOUT	-
46	C2	C2	72	A11	105	105	A11	A11	PA13 (JTMS/SWDIO)	I/O	FT	-	JTMS/SWDIO, IR_OUT, OTG_FS_NOE, SWPMI1_TX, SAI1_SD_B, EVENTOUT	-
47	B1	B1	-	-	-	-	-	-	VSS	S	-	-	-	-
48	A1	A1	73	C11	106	106	E12	E12	VDDUSB	S	-	-	-	-
-	-	-	74	F11	107	107	C12	C12	VSS	S	-	-	-	-
-	-	-	75	G11	108	108	C13	C13	VDD	S	-	-	-	-
-	-	-	-	-	-	-	E11	E11	PH6	I/O	FT	-	I2C2_SMBA, DCMI_D8, EVENTOUT	-
-	-	-	-	-	-	-	D12	D12	PH7	I/O	FT_f	-	I2C3_SCL, DCMI_D9, EVENTOUT	-
-	-	-	-	-	-	-	D11	D11	PH9	I/O	FT	-	I2C3_SMBA, DCMI_D0, EVENTOUT	-
-	-	-	-	-	-	-	B13	B13	PH12	I/O	FT	-	TIM5_CH3, DCMI_D3, EVENTOUT	-
-	-	-	-	-	-	-	A13	A13	PH14	I/O	FT	-	TIM8_CH2N, DCMI_D4, EVENTOUT	-
-	-	-	-	-	-	-	B12	B12	PH15	I/O	FT	-	TIM8_CH3N, DCMI_D11, EVENTOUT	-
-	-	-	-	-	-	-	A12	A12	PI0	I/O	FT	-	TIM5_CH4, SPI2_NSS, DCMI_D13, EVENTOUT	-

Table 15. STM32L496xx pin definitions (continued)

Pin Number									Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
LQFP64	WLCSP100	WLCSP100_SMPS	LQFP100	UFBGA132	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS					Alternate functions	Additional functions
52	C3	D4	79	C10	112	112	E9	E9	PC11	I/O	FT_l	-	QUADSPI_BK2_NCS, SPI3_MISO, USART3_RX, UART4_RX, TSC_G3_IO3, DCMI_D4, LCD_COM5/LCD_SEG29/LCD_SEG41, SDMMC1_D3, SAI2_MCLK_B, EVENTOUT	-
53	C4	C4	80	B10	113	113	F8	F8	PC12	I/O	FT_l	-	TRACED3, SPI3_MOSI, USART3_CK, UART5_TX, TSC_G3_IO4, DCMI_D9, LCD_COM6/LCD_SEG30/LCD_SEG42, SDMMC1_CK, SAI2_SD_B, EVENTOUT	-
-	B3	B3	81	C9	114	114	B8	B8	PD0	I/O	FT	-	SPI2_NSS, DFSDM1_DATIN7, CAN1_RX, FMC_D2, EVENTOUT	-
-	A3	A3	82	B9	115	115	C8	C8	PD1	I/O	FT	-	SPI2_SCK, DFSDM1_CKIN7, CAN1_TX, FMC_D3, EVENTOUT	-
54	E4	D5	83	C8	116	116	D8	D8	PD2	I/O	FT_l	-	TRACED2, TIM3_ETR, USART3_RTS_DE, UART5_RX, TSC_SYNC, DCMI_D11, LCD_COM7/LCD_SEG31/LCD_SEG43, SDMMC1_CMD, EVENTOUT	-
-	-	-	84	B8	117	117	E8	E8	PD3	I/O	FT	-	SPI2_SCK, DCMI_D5, SPI2_MISO, DFSDM1_DATIN0, USART2_CTS, QUADSPI_BK2_NCS, FMC_CLK, EVENTOUT	-
-	B4	C5	85	B7	118	118	C7	C7	PD4	I/O	FT	-	SPI2_MOSI, DFSDM1_CKIN0, USART2_RTS_DE, QUADSPI_BK2_IO0, FMC_NOE, EVENTOUT	-
-	E5	B4	86	A6	119	119	D7	D7	PD5	I/O	FT	-	USART2_TX, QUADSPI_BK2_IO1, FMC_NWE, EVENTOUT	-
-	-	-	-	-	120	120	-	-	VSS	S	-	-	-	-

Table 16. Alternate function AF0 to AF7 (for AF8 to AF15 see *Table 17*) (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
		SYS_AF	TIM1/2/5/8/ LPTIM1	TIM1/2/3/4/5	SPI2/USART2/ CAN2/TIM8/ QUADSPI	I2C1/2/3/4/ DCMI	SPI1/2/DCMI/ QUADSPI	SPI3/I2C3/ DFSDM/ COMP1/ QUADSPI	USART1/2/3
Port C	PC0	-	LPTIM1_IN1	I2C4_SCL	-	I2C3_SCL	-	DFSDM1_ DATIN4	-
	PC1	TRACED0	LPTIM1_OUT	I2C4_SDA	SPI2_MOSI	I2C3_SDA	-	DFSDM1_CKIN4	-
	PC2	-	LPTIM1_IN2	-	-	-	SPI2_MISO	DFSDM1_ CKOUT	-
	PC3	-	LPTIM1_ETR	-	-	-	SPI2_MOSI	-	-
	PC4	-	-	-	-	-	-	-	USART3_TX
	PC5	-	-	-	-	-	-	-	USART3_RX
	PC6	-	-	TIM3_CH1	TIM8_CH1	-	-	DFSDM1_CKIN3	-
	PC7	-	-	TIM3_CH2	TIM8_CH2	-	-	DFSDM1_ DATIN3	-
	PC8	-	-	TIM3_CH3	TIM8_CH3	-	-	-	-
	PC9	-	TIM8_BKIN2	TIM3_CH4	TIM8_CH4	DCMI_D3	-	I2C3_SDA	-
	PC10	TRACED1	-	-	-	-	-	SPI3_SCK	USART3_TX
	PC11	-	-	-	-	-	QUADSPI_BK 2_NCS	SPI3_MISO	USART3_RX
	PC12	TRACED3	-	-	-	-	-	SPI3_MOSI	USART3_CK
	PC13	-	-	-	-	-	-	-	-
	PC14	-	-	-	-	-	-	-	-
	PC15	-	-	-	-	-	-	-	-

6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS}.

6.1.1 Minimum and maximum values

Unless otherwise specified, the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at T_A = 25 °C and T_A = $T_A$max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean ±3σ).

6.1.2 Typical values

Unless otherwise specified, typical data are based on T_A = 25 °C, V_{DD} = V_{DDA} = 3 V. They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean ±2σ).

6.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 16*.

6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 17*.

Figure 16. Pin loading conditions

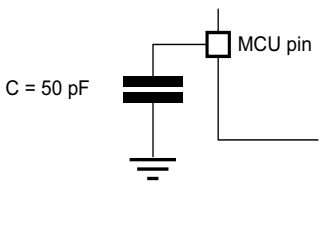


Figure 17. Pin input voltage

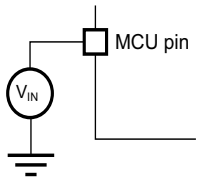


Table 19. Voltage characteristics(1)

Symbol	Ratings		Min	Max	Unit
V_{DDX} - V_{SS}	External main supply voltage (including V_{DD}, V_{DDA}, V_{DDIO2}, V_{DDUSB}, V_{LCD}, V_{BAT})		-0.3	4.0	V
VDD12 - VSS	External SMPS supply voltage	Range 1	-0.3	1.32	
		Range 2	-0.3		
V_{IN}(2)	Input voltage on FT_xxx pins		V_{SS}-0.3	min (V_{DD}, V_{DDA}, V_{DDIO2}, V_{DDUSB}, V_{LCD}) + 4.0(3)(4)	
	Input voltage on TT_xx pins		V_{SS}-0.3	4.0	
	Input voltage on BOOT0 pin		V_{SS}	9.0	
	Input voltage on any other pins		V_{SS}-0.3	4.0	
$\lvert\Delta V_{DDx}\rvert$	Variations between different V_{DDX} power pins of the same domain		-	50	mV
$\lvert V_{SSx}-V_{SS}\rvert$	Variations between all the different ground pins(5)		-	50	mV

1. All main power (V_{DD}, V_{DDA}, V_{DDIO2}, V_{DDUSB}, V_{LCD}, V_{BAT}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. V_{IN} maximum must always be respected. Refer to *Table 20: Current characteristics* for the maximum allowed injected current values.
3. This formula has to be applied only on the power supplies related to the IO structure described in the pin definition table.
4. To sustain a voltage higher than 4 V the internal pull-up/pull-down resistors must be disabled.
5. Include VREF- pin.

Table 20. Current characteristics

Symbol	Ratings	Max	Unit
ΣIV_{DD}	Total current into sum of all V_{DD} power lines (source)(1) (2)	150	mA
ΣIV_{SS}	Total current out of sum of all V_{SS} ground lines (sink)(1)	150	
$IV_{DD(PIN)}$	Maximum current into each V_{DD} power pin (source)(1)(2)	100	
$IV_{SS(PIN)}$	Maximum current out of each V_{SS} ground pin (sink)(1)	100	
$I_{IO(PIN)}$	Output current sunk by any I/O and control pin except FT_f	20	
	Output current sunk by any FT_f pin	20	
	Output current sourced by any I/O and control pin	20	
$\Sigma I_{IO(PIN)}$	Total output current sunk by sum of all I/Os and control pins(3)	100	
	Total output current sourced by sum of all I/Os and control pins(3)	100	
$I_{INJ(PIN)}$(4)	Injected current on FT_xxx, TT_xx, RST and B pins, except PA4, PA5	-5/+0(5)	
	Injected current on PA4, PA5	-5/0	
$\Sigma\lvert I_{INJ(PIN)}\rvert$	Total injected current (sum of all I/Os and control pins)(6)	25	

1. All main power (V_{DD}, V_{DDA}, V_{DDIO2}, V_{DDUSB}, V_{LCD}, V_{BAT}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supplies, in the permitted range.
2. Valid also for VDD12 on SMPS Package

Table 27. Current consumption in Run modes, code with data processing running from Flash, ART enable (Cache ON Prefetch OFF) and power supplied by external SMPS (VDD12 = 1.10 V)

Symbol	Parameter	Conditions(1)		TYP					Unit
		-	f_{HCLK}	25 °C	55 °C	85 °C	105 °C	125 °C	
I_{DD_ALL}(Run)	Supply current in Run mode	$f_{HCLK} = f_{HSE}$ up to 48MHz included, bypass mode PLL ON above 48 MHz all peripherals disable	80 MHz	3.39	3.42	3.48	3.57	3.74	mA
			72 MHz	3.06	3.09	3.15	3.24	3.43	
			64 MHz	2.74	2.76	2.81	2.91	3.10	
			48 MHz	2.06	2.08	2.14	2.23	2.42	
			32 MHz	1.39	1.41	1.46	1.56	1.74	
			24 MHz	1.06	1.07	1.13	1.22	1.40	
			16 MHz	0.72	0.74	0.79	0.88	1.06	
			8 MHz	0.39	0.41	0.46	0.56	0.75	
			4 MHz	0.22	0.24	0.29	0.39	0.58	
			2 MHz	0.14	0.16	0.21	0.30	0.50	
			1 MHz	0.10	0.11	0.16	0.26	0.46	
			100 kHz	0.06	0.07	0.13	0.22	0.42	

1. All values are obtained by calculation based on measurements done without SMPS and using following parameters: SMPS input = 3.3 V, SMPS efficiency = 85%, VDD12 = 1.10 V

Table 30. Current consumption in Run and Low-power run modes, code with data processing running from SRAM1

Symbol	Parameter	Conditions			TYP					MAX(1)					Unit
		-	Voltage scaling	f_{HCLK}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I_{DD_ALL}(Run)	Supply current in Run mode	$f_{HCLK} = f_{HSE}$ up to 48MHz included, bypass mode PLL ON above 48 MHz all peripherals disable	Range 2	26 MHz	2.72	2.76	2.89	3.12	3.58	3.0	3.1	3.4	3.8	4.8	mA
				16 MHz	1.73	1.76	1.89	2.12	2.58	1.9	2.0	2.3	2.7	3.7	
				8 MHz	0.93	0.96	1.09	1.31	1.77	1.0	1.1	1.42	1.8	2.8	
				4 MHz	0.53	0.57	0.69	0.91	1.36	0.6	0.7	0.9	1.4	2.4	
				2 MHz	0.33	0.36	0.49	0.71	1.16	0.4	0.5	0.7	1.2	2.2	
				1 MHz	0.23	0.26	0.39	0.61	1.06	0.2	0.4	0.6	1.1	2.1	
				100 kHz	0.14	0.17	0.3	0.52	0.97	0.2	0.3	0.5	1.0	2.0	
			Range 1	80 MHz	9.71	9.78	9.95	10.2	10.8	10.6	10.7	11.1	11.6	12.7	
				72 MHz	8.77	8.84	9	9.27	9.8	9.6	9.7	10.0	10.6	11.7	
				64 MHz	7.82	7.89	8.05	8.32	8.84	8.5	8.7	9.0	9.5	10.6	
				48 MHz	5.87	5.93	6.1	6.36	6.88	6.4	6.6	6.9	7.4	8.5	
				32 MHz	3.97	4.03	4.18	4.44	4.95	4.4	4.5	4.8	5.3	6.4	
				24 MHz	3.02	3.07	3.22	3.47	3.99	3.3	3.5	3.7	4.3	5.4	
				16 MHz	2.07	2.11	2.26	2.51	3.02	2.3	2.4	2.7	3.2	4.3	
I_{DD_ALL} (LPRun)	Supply current in low-power run mode	$f_{HCLK} = f_{MSI}$ all peripherals disable FLASH in power-down		2 MHz	258	296	430	665	1140	295	402	634	1154	2180	µA
				1 MHz	136	180	314	550	1020	170	283	530	1034	2065	
				400 kHz	78.5	109	241	475	951	90	206	458	958	1991	
				100 kHz	37.4	78.1	208	440	918	53	171	429	925	1957	

1. Guaranteed by characterization results, unless otherwise specified.

Table 41. Current consumption in Sleep and Low-power sleep modes, Flash ON

Symbol	Parameter	Conditions			TYP					MAX(1)					Unit
		-	Voltage scaling	f_{HCLK}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I_{DD_ALL} (Sleep)	Supply current in sleep mode,	$f_{HCLK} = f_{HSE}$ up to 48 MHz included, bypass mode pll ON above 48 MHz all peripherals disable	Range 2	26 MHz	0.79	0.82	0.95	1.17	1.63	0.9	1.0	1.2	1.7	2.7	mA
				16 MHz	0.54	0.57	0.7	0.92	1.38	0.6	0.7	1.0	1.4	2.4	
				8 MHz	0.33	0.37	0.49	0.71	1.17	0.4	0.5	0.7	1.2	2.2	
				4 MHz	0.23	0.26	0.39	0.61	1.06	0.3	0.4	0.6	1.1	2.1	
				2 MHz	0.18	0.21	0.34	0.56	1.01	0.2	0.3	0.5	1.0	1.0	
				1 MHz	0.16	0.19	0.31	0.53	0.99	0.2	0.3	0.5	1.0	1.0	
				100 kHz	0.13	0.17	0.29	0.51	0.96	0.1	0.3	0.5	1.0	1.9	
			Range 1	80 MHz	2.57	2.62	2.76	3.01	3.53	2.8	2.9	3.2	3.8	4.9	
				72 MHz	2.34	2.38	2.53	2.78	3.29	2.6	2.7	3.0	3.5	4.6	
				64 MHz	2.1	2.15	2.29	2.54	3.05	2.3	2.4	2.7	3.3	4.4	
				48 MHz	1.58	1.63	1.78	2.03	2.54	1.8	1.9	2.2	2.7	3.8	
				32 MHz	1.11	1.15	1.3	1.54	2.05	1.2	1.4	1.7	2.2	3.3	
				24 MHz	0.87	0.91	1.06	1.3	1.81	1.0	1.1	1.4	1.9	3.0	
				16 MHz	0.63	0.67	0.82	1.06	1.56	0.7	0.8	1.1	1.6	2.7	
I_{DD_ALL} (LPSleep)	Supply current in low-power sleep mode	$f_{HCLK} = f_{MSI}$ all peripherals disable		2 MHz	103	140	270	506	985	130	247	500	990	2025	µA
				1 MHz	74.2	111	245	476	955	100	215	467	963	1999	
				400 kHz	60	89.8	224	457	937	79	194	444	941	1975	
				100 kHz	53.7	84.1	216	448	928	70	185	434	933	1967	

1. Guaranteed by characterization results, unless otherwise specified.

Table 49. Current consumption in VBAT mode

Symbol	Parameter	Conditions		TYP					MAX(1)					Unit
		-	V_{BAT}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I_{DDVBAT}	Backup domain supply current	RTC disabled	1.8 V	2	18	110	329	908	-	-	-	-	-	nA
			2.4 V	2	20	125	371	1016	-	-	-	-	-	
			3 V	3	25	154	546	1965	-	-	-	-	-	
			3.6 V	10	57	324	963	2688	-	-	-	-	-	
		RTC enabled and clocked by LSE bypassed at 32768 Hz	1.8 V	198	216	312	535	-	-	-	-	-	-	
			2.4 V	280	300	411	664	-	-	-	-	-	-	
			3 V	375	402	544	943	-	-	-	-	-	-	
			3.6 V	488	529	791	1459	-	-	-	-	-	-	
		RTC enabled and clocked by LSE quartz(2)	1.8 V	320	347	448	856	1432	-	-	-	-	-	
			2.4 V	405	436	550	921	1567	-	-	-	-	-	
			3 V	512	545	686	1128	2529	-	-	-	-	-	
			3.6 V	648	705	976	1588	3293	-	-	-	-	-	

1. Guaranteed by characterization results, unless otherwise specified.
2. Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8 pF loading capacitors.

Table 50. Peripheral current consumption (continued)

Peripheral		Range 1	Range 2	Low-power run and sleep	Unit
APB2	All APB2 on	55.40	41.33	46.00	µA/MHz
ALL		234.98	195.83	235.70	

1. The BusMatrix is automatically active when at least one master is ON (CPU, DMA).
2. The GPIOx (x= A…I) dynamic current consumption is approximately divided by a factor two versus this table values when the GPIO port is locked thanks to LCKK and LCKy bits in the GPIOx_LCKR register. In order to save the full GPIOx current consumption, the GPIOx clock should be disabled in the RCC when all port I/Os are used in alternate function or analog mode (clock is only required to read or write into GPIO registers, and is not used in AF or analog modes).
3. The AHB to APB1 Bridge is automatically active when at least one peripheral is ON on the APB1.
4. The AHB to APB2 Bridge is automatically active when at least one peripheral is ON on the APB2.

The consumption for the peripherals when using SMPS can be found using STM32CubeMX PCC tool.

6.3.6 Wakeup time from low-power modes and voltage scaling transition times

The wakeup times given in *Table 51* are the latency between the event and the execution of the first user instruction.

The device goes in low-power mode after the WFE (Wait For Event) instruction.

Table 51. Low-power mode wakeup timings(1)

Symbol	Parameter	Conditions		Typ	Max	Unit
$t_{WUSLEEP}$	Wakeup time from Sleep mode to Run mode	-		6	6	Nb of CPU cycles
$t_{WULPSLEEP}$	Wakeup time from Low-power sleep mode to Low-power run mode	Wakeup in Flash with Flash in power-down during low-power sleep mode (SLEEP_PD=1 in FLASH_ACR) and with clock MSI = 2 MHz		6.6	8.3	
$t_{WUSTOP0}$	Wake up time from Stop 0 mode to Run mode in Flash	Range 1	Wakeup clock MSI = 48 MHz	7.0	11.6	µs
			Wakeup clock HSI16 = 16 MHz	6.2	10.7	
		Range 2	Wakeup clock MSI = 24 MHz	7.3	11.7	
			Wakeup clock HSI16 = 16 MHz	6.2	10.7	
			Wakeup clock MSI = 4 MHz	7.6	13.2	
	Wake up time from Stop 0 mode to Run mode in SRAM1	Range 1	Wakeup clock MSI = 48 MHz	2.5	2.9	
			Wakeup clock HSI16 = 16 MHz	2.7	2.9	
		Range 2	Wakeup clock MSI = 24 MHz	3.2	3.6	
			Wakeup clock HSI16 = 16 MHz	2.7	2.9	
			Wakeup clock MSI = 4 MHz	5.7	13.2	

High-speed internal 48 MHz (HSI48) RC oscillator

Table 60. HSI48 oscillator characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI48}	HSI48 Frequency	V_{DD}=3.0V, T_A=30°C	-	48	-	MHz
TRIM	HSI48 user trimming step	-	-	0.11(2)	0.18(2)	%
USER TRIM COVERAGE	HSI48 user trimming coverage	±32 steps	±3(3)	±3.5(3)	-	%
DuCy(HSI48)	Duty Cycle	-	45(2)	-	55(2)	%
ACC_{HSI48_REL}	Accuracy of the HSI48 oscillator over temperature (factory calibrated)	V_{DD} = 3.0 V to 3.6 V, T_A = –15 to 85 °C	-	-	±3(3)	%
		V_{DD} = 1.65 V to 3.6 V, T_A = –40 to 125 °C	-	-	±4.5(3)	
D_{VDD}(HSI48)	HSI48 oscillator frequency drift with V_{DD}	V_{DD} = 3 V to 3.6 V	-	0.025(3)	0.05(3)	%
		V_{DD} = 1.65 V to 3.6 V	-	0.05(3)	0.1(3)	
t_{su}(HSI48)	HSI48 oscillator start-up time	-	-	2.5(2)	6(2)	µs
I_{DD}(HSI48)	HSI48 oscillator power consumption	-	-	340(2)	380(2)	µA
N_T jitter	Next transition jitter Accumulated jitter on 28 cycles(4)	-	-	+/-0.15(2)	-	ns
P_T jitter	Paired transition jitter Accumulated jitter on 56 cycles(4)	-	-	+/-0.25(2)	-	ns

1. V_{DD} = 3 V, T_A = –40 to 125°C unless otherwise specified.
2. Guaranteed by design.
3. Guaranteed by characterization results.
4. Jitter measurement are performed without clock source activated in parallel.

Table 63. Flash memory characteristics(1) (continued)

Symbol	Parameter	Conditions	Typ	Max	Unit
I_{DD}	Average consumption from V_{DD}	Write mode	3.4	-	mA
		Erase mode	3.4	-	
	Maximum current (peak)	Write mode	7 (for 2 µs)	-	
		Erase mode	7 (for 41 µs)	-	

1. Guaranteed by design.

Table 64. Flash memory endurance and data retention

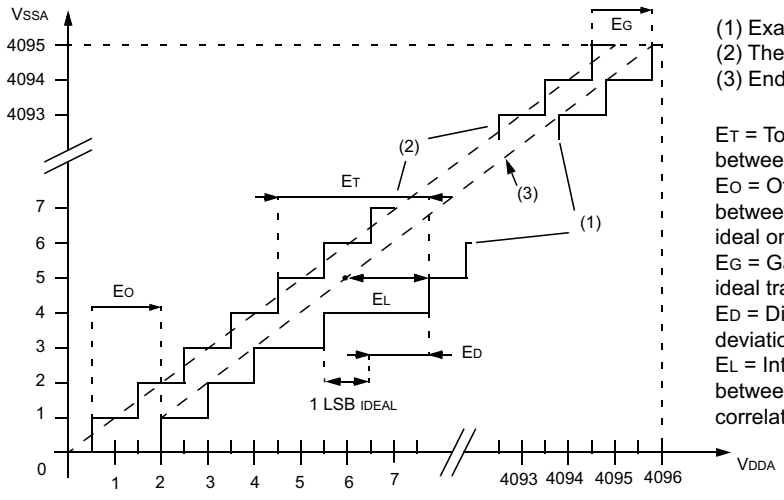
Symbol	Parameter	Conditions	Min(1)	Unit
N_{END}	Endurance	T_A = –40 to +105 °C	10	kcycles
t_{RET}	Data retention	1 kcycle(2) at T_A = 85 °C	30	Years
		1 kcycle(2) at T_A = 105 °C	15	
		1 kcycle(2) at T_A = 125 °C	7	
		10 kcycles(2) at T_A = 55 °C	30	
		10 kcycles(2) at T_A = 85 °C	15	
		10 kcycles(2) at T_A = 105 °C	10	

1. Guaranteed by characterization results.
2. Cycling performed over the whole temperature range.

Table 72. I/O AC characteristics(1)(2)

Speed	Symbol	Parameter	Conditions	Min	Max	Unit
00	Fmax	Maximum frequency	C=50 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	5	MHz
			C=50 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	1	
			C=50 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	0.1	
			C=10 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	10	
			C=10 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	1.5	
			C=10 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	0.1	
	Tr/Tf	Output rise and fall time	C=50 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	25	ns
			C=50 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	52	
			C=50 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	140	
			C=10 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	17	
			C=10 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	37	
			C=10 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	110	
01	Fmax	Maximum frequency	C=50 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	25	MHz
			C=50 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	10	
			C=50 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	1	
			C=10 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	50	
			C=10 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	15	
			C=10 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	1	
	Tr/Tf	Output rise and fall time	C=50 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	9	ns
			C=50 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	16	
			C=50 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	40	
			C=10 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	4.5	
			C=10 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	9	
			C=10 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	21	

Figure 31. ADC accuracy characteristics

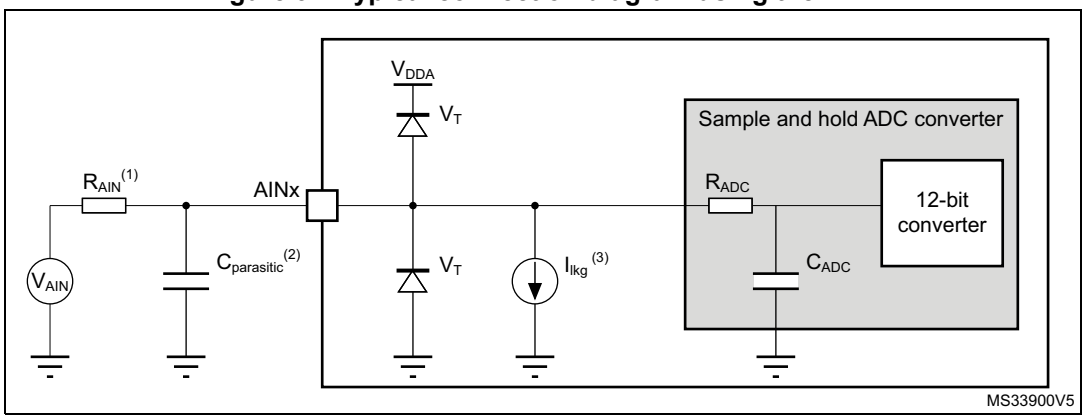


(1) Example of an actual transfer curve
(2) The ideal transfer curve
(3) End point correlation line

E_T = Total Unajusted Error: maximum deviation between the actual and ideal transfer curves.
E_O = Offset Error: maximum deviation between the first actual transition and the first ideal one.
E_G = Gain Error: deviation between the last ideal transition and the last actual one.
E_D = Differential Linearity Error: maximum deviation between actual steps and the ideal ones.
E_L = Integral Linearity Error: maximum deviation between any actual transition and the end point correlation line.

MS19880V2

Figure 32. Typical connection diagram using the ADC



MS33900V5

1. Refer to *Table 75: ADC characteristics* for the values of R_{AIN}, R_{ADC} and C_{ADC}.
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (refer to *Table 70: I/O static characteristics* for the value of the pad capacitance). A high $C_{parasitic}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.
3. Refer to *Table 70: I/O static characteristics* for the values of I_{lkg}.

General PCB design guidelines

Power supply decoupling should be performed as shown in *Figure 18: Power supply scheme*. The 10 nF capacitor should be ceramic (good quality) and it should be placed as close as possible to the chip.

Table 110. Synchronous multiplexed NOR/PSRAM read timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(CLK)}$	FMC_CLK period	$2T_{HCLK}$-0.5	-	ns
$t_{d(CLKL-NExL)}$	FMC_CLK low to FMC_NEx low (x=0..2)	-	2	
$t_{d(CLKH\_NExH)}$	FMC_CLK high to FMC_NEx high (x= 0…2)	T_{HCLK}+0.5	-	
$t_{d(CLKL-NADVL)}$	FMC_CLK low to FMC_NADV low	-	1	
$t_{d(CLKL-NADVH)}$	FMC_CLK low to FMC_NADV high	0	-	
$t_{d(CLKL-AV)}$	FMC_CLK low to FMC_Ax valid (x=16…25)	-	4.5	
$t_{d(CLKH-AIV)}$	FMC_CLK high to FMC_Ax invalid (x=16…25)	T_{HCLK}	-	
$t_{d(CLKL-NOEL)}$	FMC_CLK low to FMC_NOE low	-	1.5	
$t_{d(CLKH-NOEH)}$	FMC_CLK high to FMC_NOE high	T_{HCLK}+0.5	-	
$t_{d(CLKL-ADV)}$	FMC_CLK low to FMC_AD[15:0] valid	-	3	
$t_{d(CLKL-ADIV)}$	FMC_CLK low to FMC_AD[15:0] invalid	0	-	
$t_{su(ADV-CLKH)}$	FMC_A/D[15:0] valid data before FMC_CLK high	1	-	
$t_{h(CLKH-ADV)}$	FMC_A/D[15:0] valid data after FMC_CLK high	3.5	-	
$t_{su(NWAIT-CLKH)}$	FMC_NWAIT valid before FMC_CLK high	2	-	
$t_{h(CLKH-NWAIT)}$	FMC_NWAIT valid after FMC_CLK high	3.5	-	

1. CL = 30 pF.
2. Guaranteed by characterization results.

Figure 48. Synchronous multiplexed PSRAM write timings

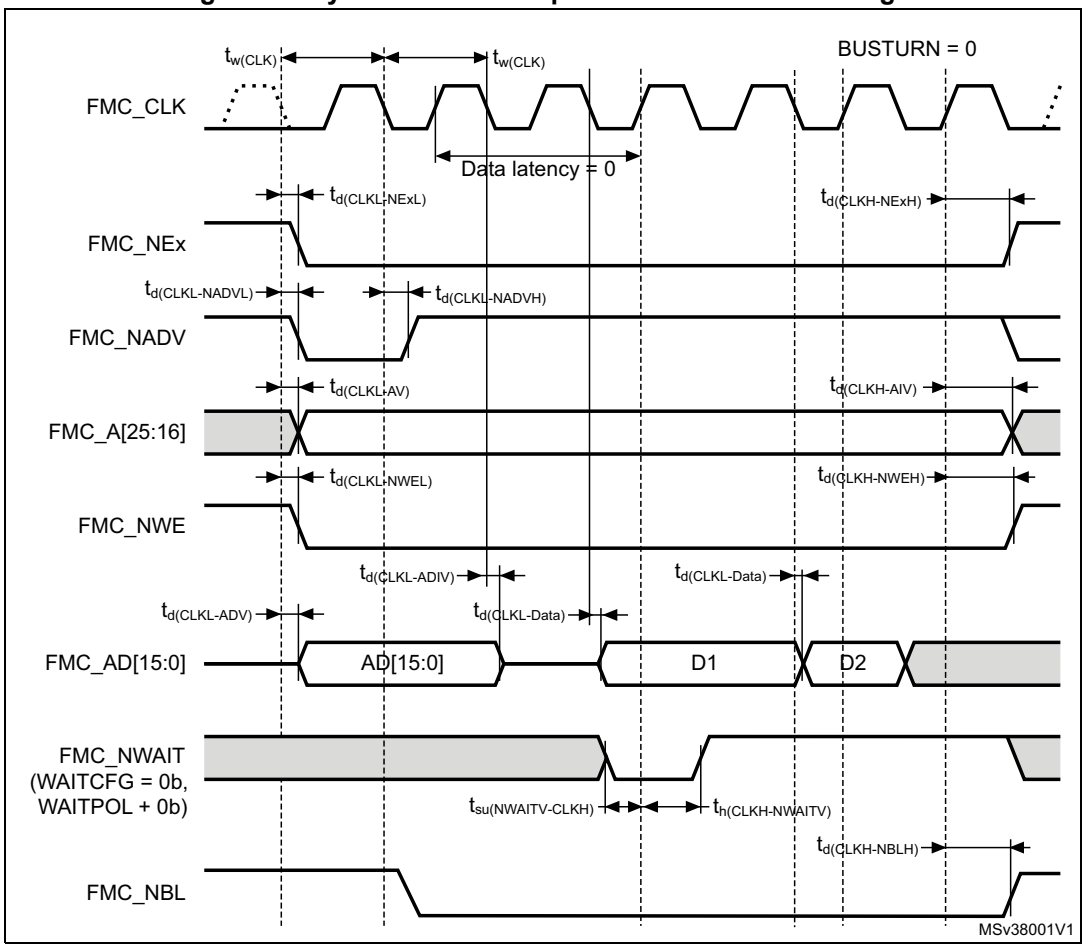


Figure 54. NAND controller waveforms for common memory write access

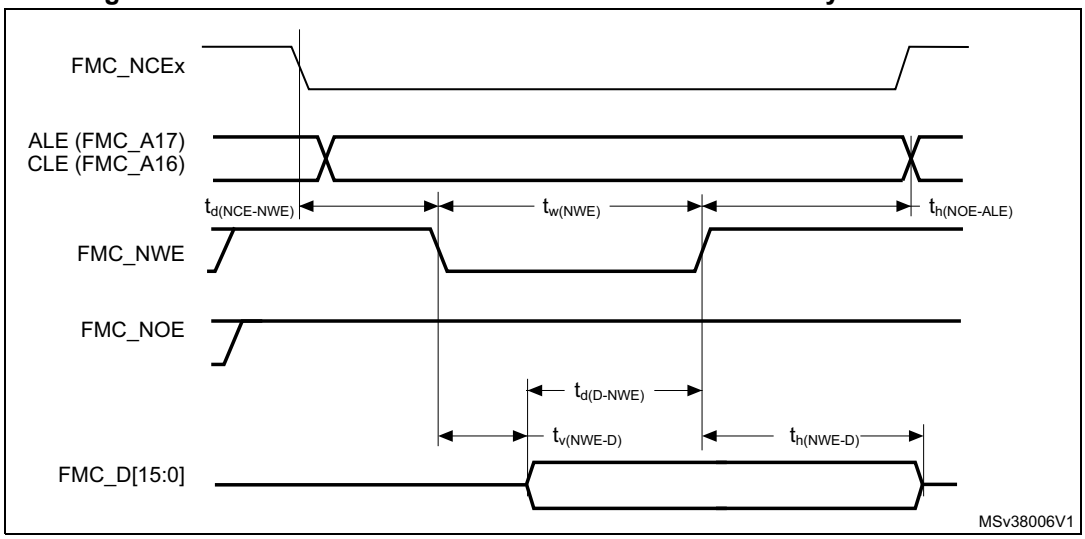


Table 114. Switching characteristics for NAND Flash read cycles(1)(2)

Symbol	Parameter	Min	Max	Unit
$T_{w(N0E)}$	FMC_NOE low width	$4T_{HCLK}$-0.5	$4T_{HCLK}$+0.5	ns
$T_{su(D-NOE)}$	FMC_D[15-0] valid data before FMC_NOE high	12	-	
$T_{h(NOE-D)}$	FMC_D[15-0] valid data after FMC_NOE high	0	-	
$T_{d(NCE-NOE)}$	FMC_NCE valid before FMC_NOE low	-	$3T_{HCLK}$+1	
$T_{h(NOE-ALE)}$	FMC_NOE high to FMC_ALE invalid	$4T_{HCLK}$-2	-	

1. CL = 30 pF.
2. Guaranteed by characterization results.

Table 115. Switching characteristics for NAND Flash write cycles(1)(2)

Symbol	Parameter	Min	Max	Unit
$T_{w(NWE)}$	FMC_NWE low width	$4T_{HCLK}$-0.5	$4T_{HCLK}$+0.5	ns
$T_{v(NWE-D)}$	FMC_NWE low to FMC_D[15-0] valid	5	-	
$T_{h(NWE-D)}$	FMC_NWE high to FMC_D[15-0] invalid	$2T_{HCLK}$-1	-	
$T_{d(D-NWE)}$	FMC_D[15-0] valid before FMC_NWE high	$5T_{HCLK}$-1	-	
$T_{d(NCE\_NWE)}$	FMC_NCE valid before FMC_NWE low	-	$3T_{HCLK}$+1	
$T_{h(NWE-ALE)}$	FMC_NWE high to FMC_ALE invalid	$2T_{HCLK}$-2	-	

1. CL = 30 pF.
2. Guaranteed by characterization results.

The following examples show how to calculate the temperature range needed for a given application.

Example 1: High-performance application

Assuming the following application conditions:

Maximum ambient temperature T_{Amax} = 82 °C (measured according to JESD51-2), I_{DDmax} = 50 mA, V_{DD} = 3.5 V, maximum 20 I/Os used at the same time in output at low level with I_{OL} = 8 mA, V_{OL}= 0.4 V and maximum 8 I/Os used at the same time in output at low level with I_{OL} = 20 mA, V_{OL}= 1.3 V

P_{INTmax} = 50 mA × 3.5 V= 175 mW

P_{IOmax} = 20 × 8 mA × 0.4 V + 8 × 20 mA × 1.3 V = 272 mW

This gives: P_{INTmax} = 175 mW and P_{IOmax} = 272 mW:

P_{Dmax} = 175 + 272 = 447 mW

Using the values obtained in *Table 129* T_{Jmax} is calculated as follows:

– For LQFP100, 42 °C/W

T_{Jmax} = 82 °C + (42 °C/W × 447 mW) = 82 °C + 18.774 °C = 100.774 °C

This is within the range of the suffix 6 version parts (–40 < T_J < 105 °C) see *Section 8: Part numbering*.

In this case, parts must be ordered at least with the temperature range suffix 6 (see Part numbering).

Note: With this given P_{Dmax} we can find the T_{Amax} allowed for a given device temperature range (order code suffix 6 or 7).

Suffix 6: T_{Amax} = T_{Jmax} - (42°C/W × 447 mW) = 105-18.774 = 86.226 °C

Suffix 7: T_{Amax} = T_{Jmax} - (42°C/W × 447 mW) = 125-18.774 = 106.226 °C

Example 2: High-temperature application

Using the same rules, it is possible to address applications that run at high ambient temperatures with a low dissipation, as long as junction temperature T_J remains within the specified range.

Assuming the following application conditions:

Maximum ambient temperature T_{Amax} = 100 °C (measured according to JESD51-2), I_{DDmax} = 20 mA, V_{DD} = 3.5 V, maximum 20 I/Os used at the same time in output at low level with I_{OL} = 8 mA, V_{OL}= 0.4 V

P_{INTmax} = 20 mA × 3.5 V= 70 mW

P_{IOmax} = 20 × 8 mA × 0.4 V = 64 mW

This gives: P_{INTmax} = 70 mW and P_{IOmax} = 64 mW:

P_{Dmax} = 70 + 64 = 134 mW

Thus: P_{Dmax} = 134 mW

Using the values obtained in *Table 129* T_{Jmax} is calculated as follows:

– For LQFP100, 42 °C/W

T_{Jmax} = 100 °C + (42 °C/W × 134 mW) = 100 °C + 5.628 °C = 105.628 °C

This is above the range of the suffix 6 version parts (–40 < T_J < 105 °C).